



MCH3320

P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-100	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		-0.3	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-1.2	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² X0.8mm)	0.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0	-100			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-150mA	0.2	0.45		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-150mA, V _{GS} =-10V		3.0	3.9	Ω
	R _{DS(on)2}	I _D =-150mA, V _{GS} =-4V		3.6	5.0	Ω
Input Capacitance	C _{iss}	V _{DS} =-20V, f=1MHz		78		pF
Output Capacitance	C _{oss}	V _{DS} =-20V, f=1MHz		6.0		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-20V, f=1MHz		4.0		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		6.0		ns
Rise Time	t _r	See specified Test Circuit.		3.0		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		16		ns
Fall Time	t _f	See specified Test Circuit.		16		ns

Marking : JV

Continued on next page.

■ Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

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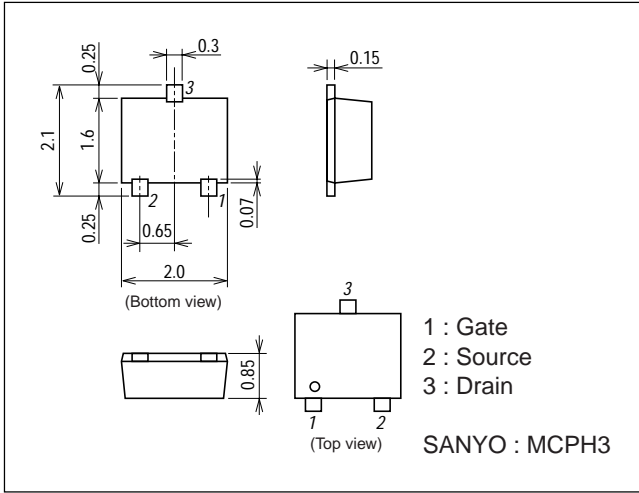
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	$V_{DS}=-50V, V_{GS}=-10V, I_D=-0.3A$		3.0		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-50V, V_{GS}=-10V, I_D=-0.3A$		0.5		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-50V, V_{GS}=-10V, I_D=-0.3A$		0.5		nC
Diode Forward Voltage	VSD	$I_S=-0.3A, V_{GS}=0$		-0.87	-1.2	V

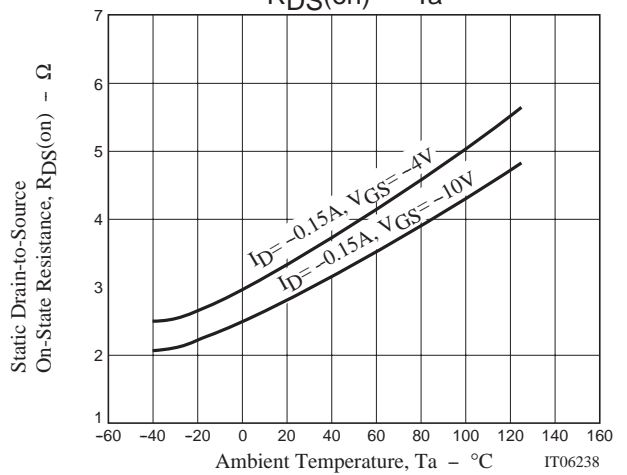
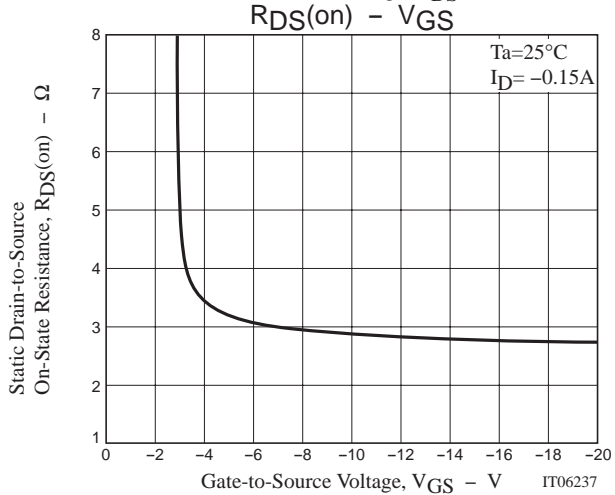
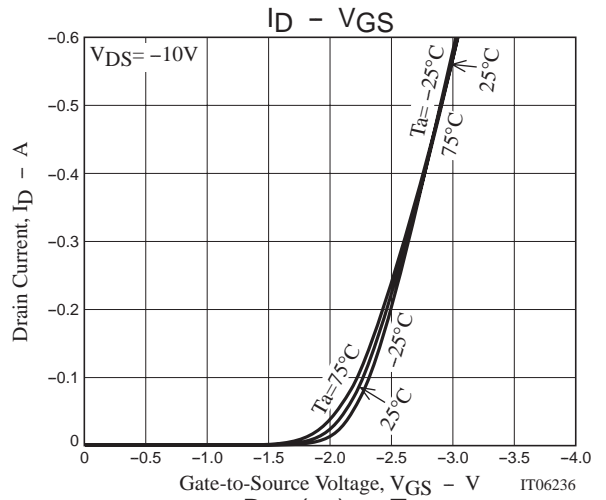
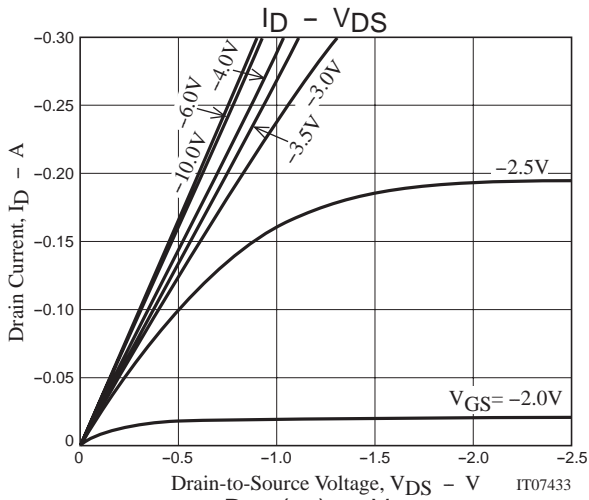
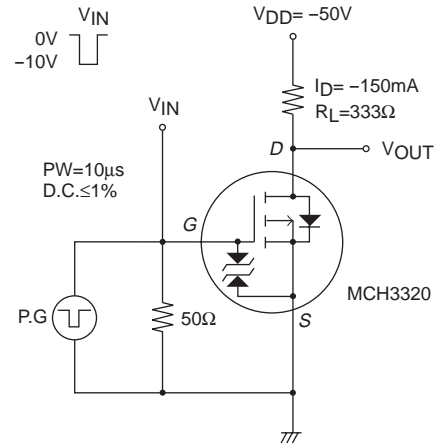
Package Dimensions

unit : mm

2167A



Switching Time Test Circuit



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